

connected to the semiconductor layer through a contact hole provided in the first wiring and the first insulating film. This is shown, for example, in Figs. 3C, 9B, 14 and 16 of the present application.

Neither Yamazaki '818 nor Zhang '701 disclose or suggest this feature. Instead, the alleged first and second wirings in each reference are not located in such proximity that the second wiring can be directly connected to the semiconductor layer through a contact hole provided in the first wiring and the first insulating film. Hence, for at least this reason, the rejected claims are patentable over these references.

Further, Applicants have amended independent Claim 40 to recite that the pixel electrode is connected to the second wiring at the bottom of a contact hole provided in the second insulating film, in order to further clarify the claimed invention.

Accordingly, for at least the above-stated reasons, it is requested that these §102 rejections now be withdrawn.

#### Claim Rejections – 35 USC §103

The Examiner also continues to reject Claims 1-12, 19-24, 28-33, 41-43 and 45 under 35 USC §103 as being unpatentable over Zhang '701 in view of Yamazaki '542. The Examiner also continues to reject Claims 1-12, 19-24 and 28-45 under 35 USC §103 as being unpatentable over Yano et al. in view of Yamazaki '542. Each of these rejections is respectfully traversed.

In order to advance the prosecution of this application, Applicants have amended the independent claims in a manner similar to that of Claim 40 to claim a direct connection of the second (metallic or conductive) layer through a contact hole in the first (metallic or conductive) layer and the first insulating film. Applicants have also amended the independent claims to

recite that the pixel electrode is connected to the second (metallic or conductive) layer at the bottom of a contact hole.

As explained above, these features are not disclosed or suggested by Zhang '701 (nor Yamazaki '542 which is cited by the Examiner for a different reason). Hence, the claims are patentable over these references, and it is requested that the §103 rejection over these references be withdrawn.

With regard to the rejection over Yano and Yamazaki '542, Yano does not indicate that electrode 43B is a pixel electrode, and there is no disclosure in Yano of a pixel electrode, as required in the claimed invention. Further, electrode 43B in Yano appears to be connected to an electrode 42B at the top of a contact hole formed in insulating film 23, which is different than the claimed invention which recites the pixel electrode is connected to the second (metallic or conductive) layer at the bottom of a contact hole. Therefore, Yano (and Yamazaki '542 which is cited by the Examiner for a different reason) does not disclose or suggest the claimed invention.

Hence, the claims are patentable over these references, and it is requested that the §103 rejection over these references be withdrawn.

For at least the above-stated reasons, it is respectfully submitted that the claimed invention is patentable over the cited references, and it is requested that the §§102 and 103 rejections be withdrawn.

#### Conclusion

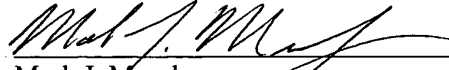
It is respectfully submitted that the present application is in a condition for allowance and should be allowed.

If any fee is due for this amendment, please charge our deposit account 50/1039.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

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Marked-up copy of the amendments made herein:

**IN THE CLAIMS:**

Please amend the claims as follows:

1. (Third Amendment) A semiconductor device comprising:  
a first insulating film comprising an organic material formed over a conductive layer;  
a first metallic layer formed on said first insulating film;  
a second metallic layer formed on said first metallic layer;  
a second insulating film formed on said second metallic layer; and  
a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer [through] at the bottom of a contact hole provided in said second insulating film,

wherein said conductive layer and said second metallic layer are directly connected to each other [at the bottom of] through a contact hole provided in said first metallic layer and said first insulating film.

7. (Third Amendment) A semiconductor device comprising:  
a first insulating film comprising an organic material formed over a thin film transistor;  
a first metallic layer formed on said first insulating film;  
a second metallic layer formed on said first metallic layer;  
a second insulating film formed on said second metallic layer; and  
a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second metallic layer [through] at the bottom of a contact hole provided in said second insulating film,

wherein a source region or a drain region of said thin film transistor and said second metallic layer are directly connected to each other [at the bottom of] through a contact hole provided in said first metallic layer and said first insulating film.

19. (Third Amendment) A semiconductor device comprising:  
a first insulating film comprising an organic material formed over a thin film transistor;  
a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;  
a second insulating film formed on said second conductive layer; and  
a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer [through] at the bottom of a contact hole provided in said second insulating film,

wherein a source region or a drain region and said second conductive layer are directly connected to each other [at the bottom of] through a contact hole provided in said first conductive layer and said first insulating film,

wherein said second conductive layer is contact with said first insulating film inside of said contact hole[s].

28. (Fourth Amendment) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film [comprising an organic material] formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer [through] at the bottom of a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer through a contact hole provided in said first conductive layer and said first insulating film.

34. (Fourth Amendment) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film comprising an organic material formed over said thin film transistor;

a first conductive layer formed on said first insulating film;

a second conductive layer formed on said first conductive layer;

a second insulating film formed on said second conductive layer; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second conductive layer [through] at the bottom of a contact hole provided in said second insulating film,

wherein said second conductive layer is directly connected to said semiconductor layer through a contact hole provided in said first conductive layer and said first insulating film.

40. (Twice Amended) A semiconductor device comprising:

a thin film transistor formed over a substrate, said thin film transistor having a semiconductor layer and a gate electrode adjacent to said semiconductor layer with a gate insulating film interposed therebetween;

a first insulating film formed over said thin film transistor;

a first wiring formed on said first insulating film;

a second wiring formed on said first wiring;

a second insulating film formed on said second wiring; and

a pixel electrode formed on said second insulating film, said pixel electrode being connected to said second wiring [through] at the bottom of a contact hole provided in said second insulating film,

wherein said second wiring is directly connected to said semiconductor layer through a contact hole provided in said first wiring and said first insulating film.